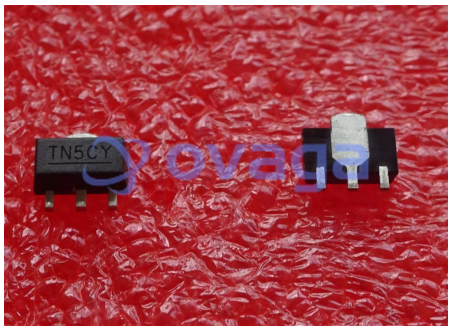
TN2524N8-G

Data Sheet

Trans MOSFET N-CH Si 240V 0.36A 4-Pin(3+Tab) SOT-89 T/R

Manufacturers	Microchip Technology, Inc
Package/Case	SOT-89
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for TN2524N8-G or Email to us: sales@ovaga.com We will contact you in 12 hours. RFQ

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure andwell-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.Vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Features

Low threshold (2.0V max.)

High input impedance

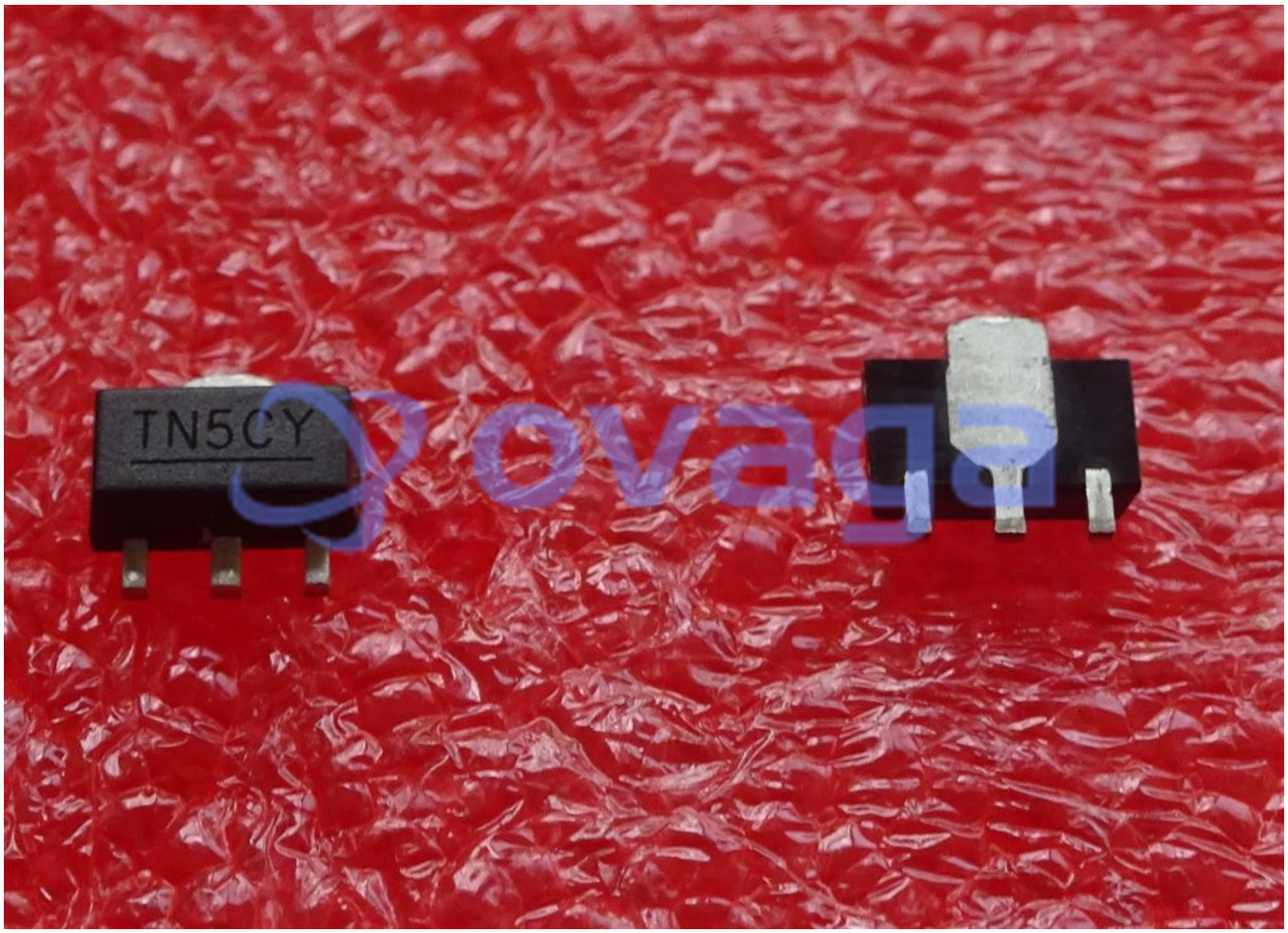
Low input capacitance (125pF max.)

Fast switching speeds

Low on-resistance

Free from secondary breakdown

Low input and output leakage



Related Products

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SOIC-8

[DN3525N8-G](#)

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SOT-89-3

[DN3135K1-G](#)

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SOT-23 (TO-236AB)

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97A/200V/MOS/1U

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DIP-18